

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2223-4** is Designed for General Purpose Clacc C Applications up to 2.3 GHz.

FEATURES:

- Internal Input/Output Matching Networks
- $P_G = 8.0$ dB at 4.0 W/2.3 GHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.75 A
V_{CC}	26 V
P_{DISS}	15.9 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	11.0 °C/W

PACKAGE STYLE .400 2NL FLG

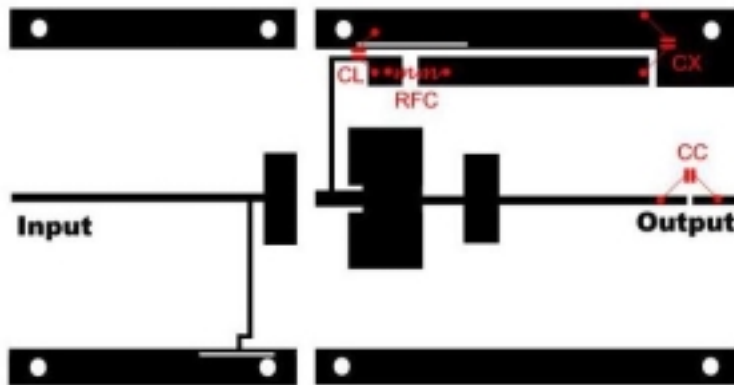
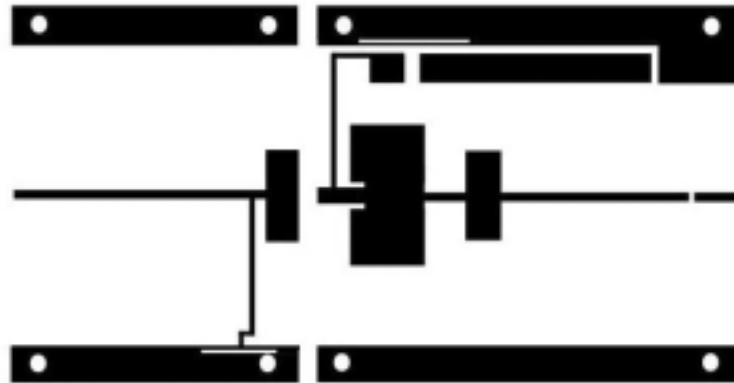
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F	.193 / 4.90	
G	.450 / 11.43	
H	.125 / 3.18	
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10531

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 5.0$ mA	40			V
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10$ Ω	40			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 22$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	10		100	---
P_G	$V_{CC} = 22$ V $P_{OUT} = 4.0$ W $f = 2.2 - 2.3$ GHz	8.0			dB
η_c		40			%

TEST BOARD



1"

CC = 100 pF Ceramic Chip
 CL = 100 pF Ceramic Chip
 CX = 100 pF Ceramic Chip and 5 microF Electrolytic
 RFC = 8 turns #28 AWG 0.010" dia.